

IN THE ABSTRACT

Please amend the Abstract at page 33, lines 3-13, as follows:

A method of and device for ~~simulation which represents~~ simulating variations in electrical characteristics (~~I_{dsat} , V_{th} and the like~~) of a ~~device constituting a~~ semiconductor integrated circuit ~~in the form of~~ by using a corner model including corners defining the limits of the variations ~~is provided~~. A circuit simulation is performed to determine device parameter sensitivities, which are the derivatives of the electrical characteristics with respect to device parameters ~~such as ΔL , ΔW , T_{ox} and V_{th0}~~ . Variations in the device parameters at each corner are determined by applying the device parameter sensitivities and the values of the electrical characteristics ~~required for~~ at each corner to the normal equation ~~of the linear of~~ the least squares method. The method and device can uniquely determine the values of a set of device parameters at each corner without the need to repeat the circuit simulation ~~and can uniquely determine the values of the set of device parameters~~.